

Silicon PNP Power Transistors

2SB940,2SB940A

DESCRIPTION

- With TO-220Fa package
- Complement to type 2SD1264/1264A
- High collector to emitter voltage V_{CEO}
- Large collector power dissipation P_C

APPLICATIONS

- For power amplification
- For TV vertical deflection output

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

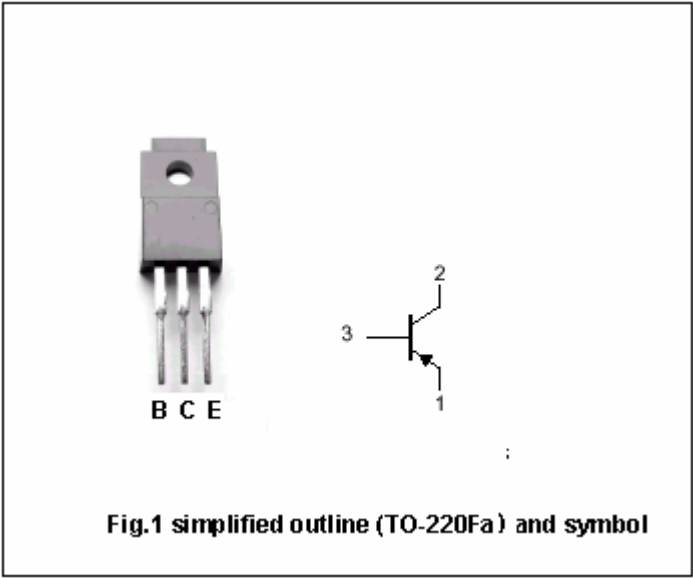


Fig.1 simplified outline (TO-220Fa) and symbol

Absolute maximum ratings($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SB940	Open emitter	-200	V
		2SB940A		-200	
V_{CEO}	Collector-emitter voltage	2SB940	Open base	-150	V
		2SB940A		-180	
V_{EBO}	Emitter-base voltage		Open collector	-6	V
I_C	Collector current			-2	A
I_{CM}	Collector current-peak			-3	A
P_C	Collector power dissipation	$T_a=25^{\circ}\text{C}$		2	W
		$T_C=25^{\circ}\text{C}$		30	
T_j	Junction temperature			150	$^{\circ}\text{C}$
T_{stg}	Storage temperature			-55~150	$^{\circ}\text{C}$

Silicon PNP Power Transistors

2SB940,2SB940A

CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SB940	$I_C=-5mA, I_B=0$	-150			V
		2SB940A		-180			
$V_{(BR)CBO}$	Collector-base breakdown voltage		$I_C=-50\mu A, I_E=0$	-200			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage		$I_C=-500\mu A, I_C=0$	-6			V
V_{CEsat}	Collector-emitter saturation voltage		$I_C=-0.5A, I_B=-50mA$			-1.0	V
V_{BE}	Base-emitter voltage		$I_C=-0.4A; V_{CE}=-10V$			-1.0	V
I_{EBO}	Emitter cut-off current		$V_{EB}=-4V; I_C=0$			-50	μA
I_{CBO}	Collector cut-off current		$V_{CB}=-200V; I_E=0$			-50	μA
h_{FE-1}	DC current gain		$I_C=-0.15A; V_{CE}=-10V$	60		240	
h_{FE-2}	DC current gain		$I_C=-0.4A; V_{CE}=-10V$	50			
f_T	Transition frequency		$I_C=-0.5A; V_{CE}=-10V, f=10MHz$		30		MHz

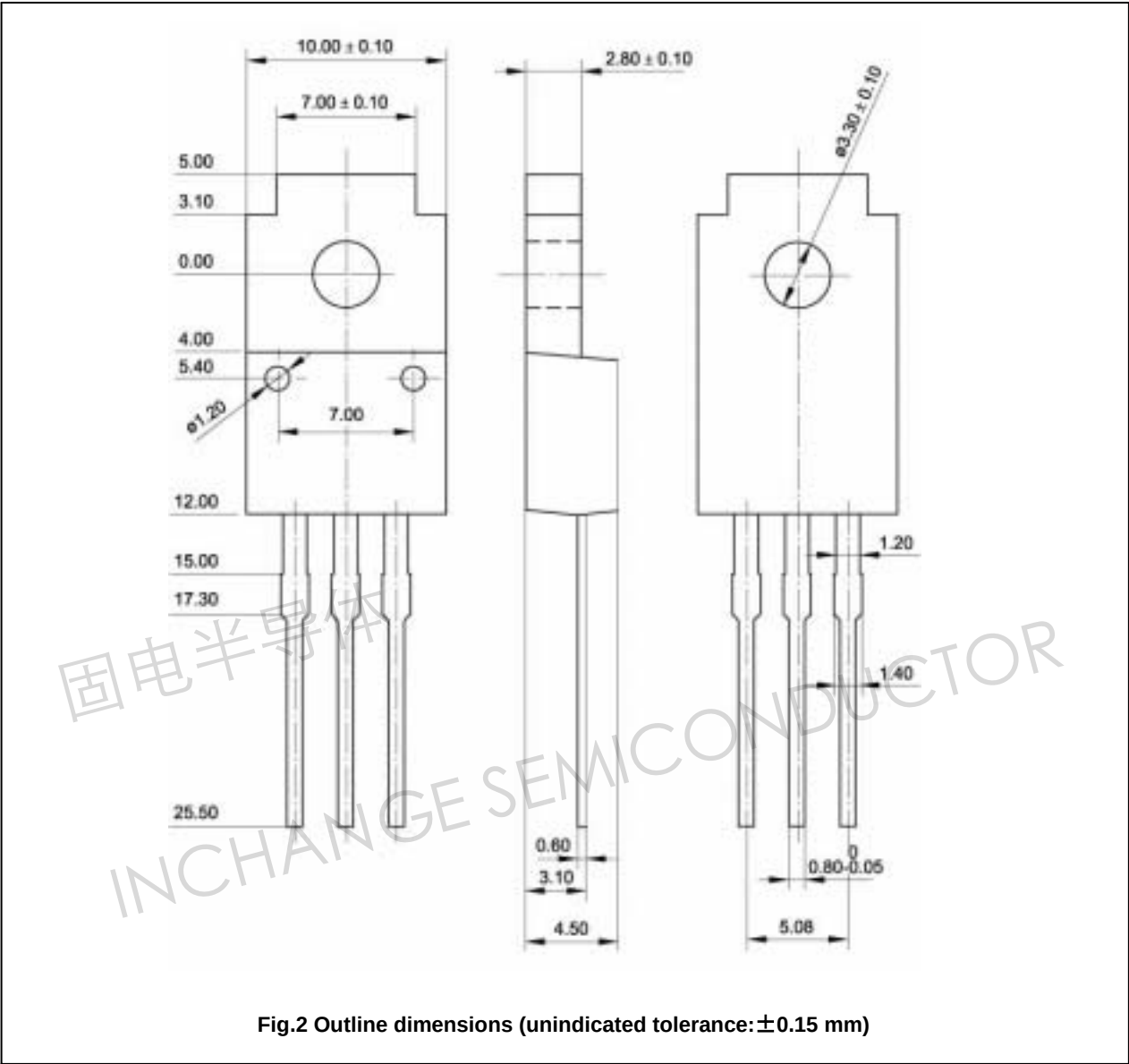
◆ h_{FE-1} Classifications

Q	P
60-140	100-240

Silicon PNP Power Transistors

2SB940,2SB940A

PACKAGE OUTLINE



Silicon PNP Power Transistors

2SB940, 2SB940A

